

ISOLATION FOR SOI CHIP WITH MULTIPLE
SILICON FILM THICKNESSES

Abstract of the Disclosure

[00050] A semiconductor-on-insulator chip is provided which includes a substrate that is formed of an electrically insulating material; a semiconducting layer overlying the substrate; a first region in the semiconducting layer that has a first thickness, the first region includes silicon regions defined by a shallow trench isolation; and a second region in the semiconducting layer that has a second thickness, the second region includes active regions defined by mesa isolation.

FIG. 6